

NLAS4599

Low Voltage Single Supply SPDT Analog Switch

The NLAS4599 is an advanced high speed CMOS single pole – double throw analog switch fabricated with silicon gate CMOS technology. It achieves high speed propagation delays and low ON resistances while maintaining low power dissipation. This switch controls analog and digital voltages that may vary across the full power–supply range (from V_{CC} to GND).

The device has been designed so the ON resistance (R_{ON}) is much lower and more linear over input voltage than R_{ON} of typical CMOS analog switches.

The channel select input is compatible with standard CMOS outputs.

The channel select input structure provides protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. This input structure helps prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

- Channel Select Input Over–Voltage Tolerant to 5.5 V
- Fast Switching and Propagation Speeds
- Break–Before–Make Circuitry
- Low Power Dissipation: $I_{CC} = 2 \mu\text{A}$ (Max) at $T_A = 25^\circ\text{C}$
- Diode Protection Provided on Channel Select Input
- Improved Linearity and Lower ON Resistance over Input Voltage
- Latch–up Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V; Machine Model > 200 V
- Chip Complexity: 38 FETs
- Pb–Free Packages are Available

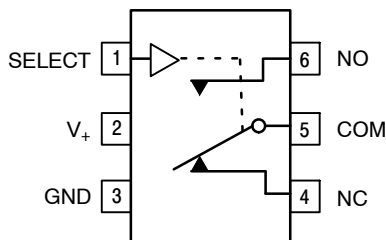


Figure 1. Pin Assignment



Figure 2. Logic Symbol

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



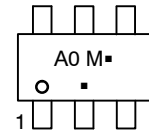
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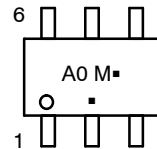
MARKING DIAGRAMS



TSOP-6
DT SUFFIX
CASE 318G



SC-88
DF SUFFIX
CASE 419B



A0 = Specific Device Code
M = Date Code
▪ = Pb–Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

FUNCTION TABLE

Select	ON Channel
L	NC
H	NO

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage	-0.5 to +7.0	V
V _{IS}	Analog Input Voltage (V _{NO} or V _{COM})	-0.5 ≤ V _{IS} ≤ V _{CC} + 0.5	V
V _{IN}	Digital Select Input Voltage	-0.5 ≤ V _I ≤ + 7.0	V
I _{IK}	DC Current, Into or Out of Any Pin	± 50	mA
P _D	Power Dissipation in Still Air	SC-88 200 TSOP-6 200	mW
T _{STG}	Storage Temperature Range	-65 to +150	°C
T _L	Lead Temperature, 1mm from Case for 10 seconds	260	°C
T _J	Junction Temperature Under Bias	150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) 2000 Machine Model (Note 2) 200 Charged Device Model (Note 3) N/A	V
I _{LATCH-UP}	Latch-Up Performance	Above V _{CC} and Below GND at 125°C (Note 4)	± 300 mA
θ _{JA}	Thermal Resistance	SC-88 333 TSOP-6 333	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Tested to EIA/JESD22-A114-A
2. Tested to EIA/JESD22-A115-A
3. Tested to JESD22-C101-A
4. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{IN}	Digital Select Input Voltage	GND	5.5	V
V _{IS}	Analog Input Voltage (NC, NO, COM)	GND	V _{CC}	V
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Rise or Fall Time, SELECT	V _{CC} = 3.3 V ± 0.3 V 0 V _{CC} = 5.0 V ± 0.5 V 0	100 20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

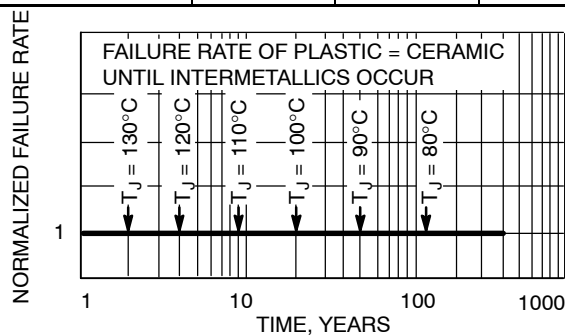


Figure 3. Failure Rate vs. Time Junction Temperature

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DC CHARACTERISTICS – Digital Section (Voltages Referenced to GND)

Symbol	Parameter	Condition	V _{CC}	Guaranteed Limit			Unit
				-55 to 25°C	<85°C	<125°C	
V _{IH}	Minimum High-Level Input Voltage, Select Input		2.0	1.5	1.5	1.5	V
			2.5	1.9	1.9	1.9	
			3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			5.5	3.85	3.85	3.85	
V _{IL}	Maximum Low-Level Input Voltage, Select Input		2.0	0.5	0.5	0.5	V
			2.5	0.6	0.6	0.6	
			3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			5.5	1.65	1.65	1.65	
I _{IN}	Maximum Input Leakage Current, Select Input	V _{IN} = 5.5 V or GND	5.5	±0.1	±1.0	±1.0	μA
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or GND	0	±10	±10	±10	μA
I _{CC}	Maximum Quiescent Supply Current	Select and V _{IS} = V _{CC} or GND	5.5	1.0	1.0	2.0	μA

DC ELECTRICAL CHARACTERISTICS – Analog Section

Symbol	Parameter	Condition	V _{CC}	Guaranteed Limit			Unit
				-55 to 25°C	<85°C	<125°C	
R _{ON}	Maximum “ON” Resistance (Figures 17 – 23)	V _{IN} = V _{IL} or V _{IH} V _{IS} = GND to V _{CC} I _{IN} ≤ 10.0 mA	2.5	85	95	105	Ω
			3.0	45	50	55	
			4.5	30	35	40	
			5.5	25	30	35	
R _{FLAT (ON)}	ON Resistance Flatness (Figures 17 – 23)	V _{IN} = V _{IL} or V _{IH} I _{IN} ≤ 10.0 mA V _{IS} = 1V, 2V, 3.5V	4.5	4	4	5	Ω
ΔR _{ON (ON)}	ON Resistance Match Between Channels	V _{IN} = V _{IL} or V _{IH} I _{IN} ≤ 10.0 mA V _{NO} or V _{NC} = 3.5 V	4.5	2	2	3	Ω
I _{NC(OFF)} I _{NO(OFF)}	NO or NC Off Leakage Current (Figure 9)	V _{IN} = V _{IL} or V _{IH} V _{NO} or V _{NC} = 1.0 V _{COM} 4.5 V	5.5	1	10	100	nA
I _{COM(ON)}	COM ON Leakage Current (Figure 9)	V _{IN} = V _{IL} or V _{IH} V _{NO} 1.0 V or 4.5 V with V _{NC} floating or V _{NO} 1.0 V or 4.5 V with V _{NO} floating V _{COM} = 1.0 V or 4.5 V	5.5	1	10	100	nA

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AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

Symbol	Parameter	Test Conditions	V _{CC} (V)	V _{IS} (V)	Guaranteed Max Limit						Unit	
					-55 to 25°C			<85°C		<125°C		
					Min	Typ*	Max	Min	Max	Min		Max
t _{ON}	Turn-On Time (Figures 12 and 13)	R _L = 300 Ω, C _L = 35 pF (Figures 5 and 6)	2.5	2.0	5	23	28	5	30	5	30	ns
			3.0	2.0	5	16	21	5	25	5	25	
			4.5	3.0	2	11	16	2	20	2	20	
			5.5	3.0	2	9	14	2	20	2	20	
t _{OFF}	Turn-Off Time (Figures 12 and 13)	R _L = 300 Ω, C _L = 35 pF (Figures 5 and 6)	2.5	2.0	1	7	12	1	15	1	15	ns
			3.0	2.0	1	5	10	1	15	1	15	
			4.5	3.0	1	4	9	1	12	1	12	
			5.5	3.0	1	3	8	1	12	1	12	
t _{BBM}	Minimum Break-Before-Make Time	V _{IS} = 3.0 V (Figure 4) R _L = 300 Ω, C _L = 35 pF	2.5	2.0	1	12		1		1		ns
			3.0	2.0	1	11		1		1		
			4.5	3.0	1	6		1		1		
			5.5	3.0	1	5		1		1		

*Typical Characteristics are at 25°C.

		Typical @ 25, V _{CC} = 5.0 V	
C _{IN}	Maximum Input Capacitance, Select Input	8	pF
C _{NO} or C _{NC}	Analog I/O (switch off)	10	
C _{COM}	Common I/O (switch off)	10	
C _(ON)	Feedthrough (switch on)	20	

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

Symbol	Parameter	Condition	V _{CC} (V)	Typical	Unit
				25°C	
BW	Maximum On-Channel -3dB Bandwidth or Minimum Frequency Response (Figure 10)	V _{IN} = 0 dBm V _{IN} centered between V _{CC} and GND (Figure 7)	3.0	170	MHz
			4.5	200	
			5.5	200	
V _{ONL}	Maximum Feedthrough On Loss	V _{IN} = 0 dBm @ 100 kHz to 50 MHz V _{IN} centered between V _{CC} and GND (Figure 7)	3.0	-3	dB
			4.5	-3	
			5.5	-3	
V _{ISO}	Off-Channel Isolation (Figure 10)	f = 100 kHz; V _{IS} = 1 V RMS V _{IN} centered between V _{CC} and GND (Figure 7)	3.0	-93	dB
			4.5	-93	
			5.5	-93	
Q	Charge Injection Select Input to Common I/O (Figure 15)	V _{IN} = V _{CC} to GND, F _{IS} = 20 kHz t _r = t _f = 3 ns R _{IS} = 0 Ω, C _L = 1000 pF Q = C _L * ΔV _{OUT} (Figure 8)	3.0	1.5	pC
			5.5	3.0	
THD	Total Harmonic Distortion THD + Noise (Figure 14)	F _{IS} = 20 Hz to 100 kHz, R _L = R _{gen} = 600 Ω, C _L = 50 pF V _{IS} = 5.0 V _{PP} sine wave	5.5	0.1	%

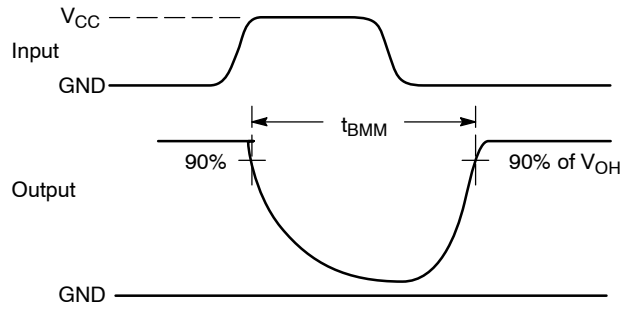
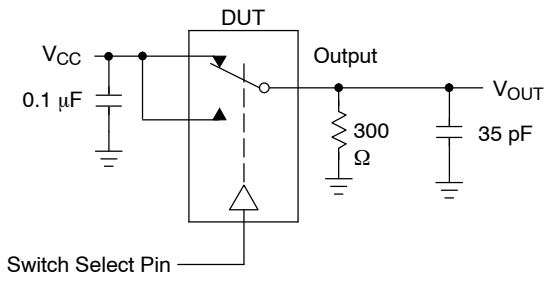


Figure 4. t_{BMM} (Time Break-Before-Make)

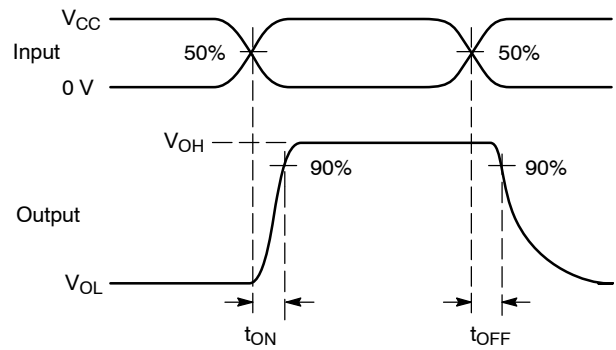
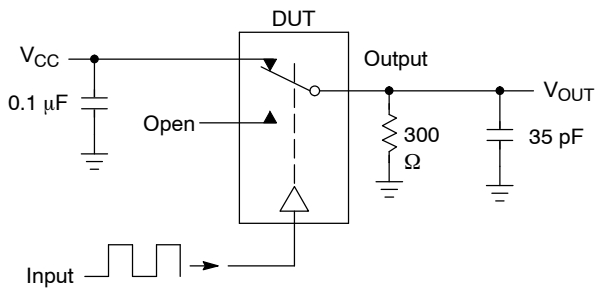


Figure 5. t_{ON}/t_{OFF}

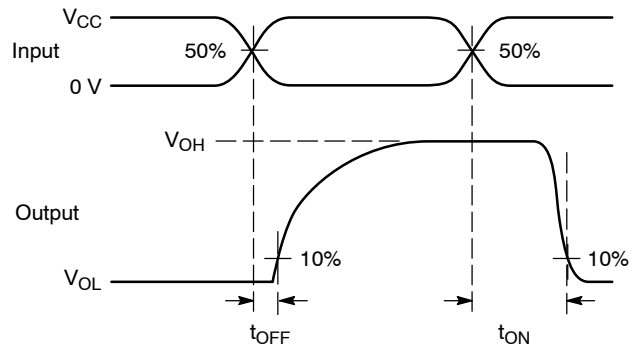
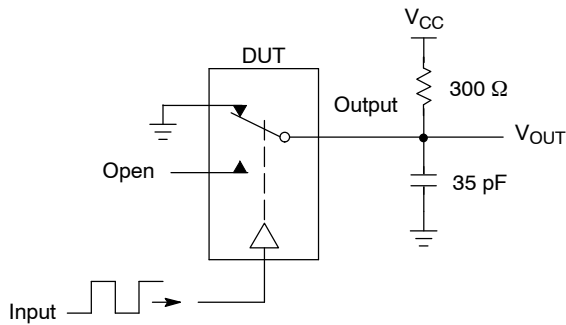


Figure 6. t_{ON}/t_{OFF}

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Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz}$$

$$V_{ONL} = \text{On Channel Loss} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz to } 50 \text{ MHz}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

Figure 7. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/ V_{ONL}



Figure 8. Charge Injection: (Q)

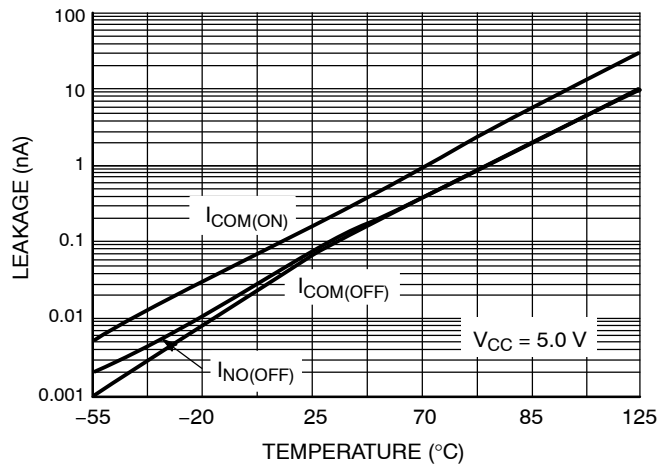


Figure 9. Switch Leakage vs. Temperature

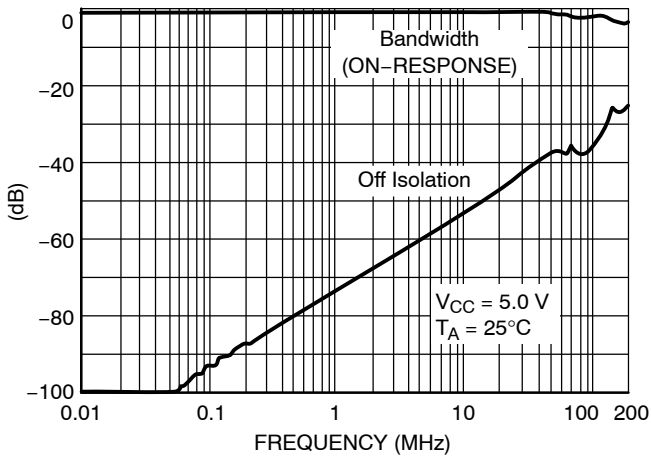


Figure 10. Bandwidth and Off-Channel Isolation

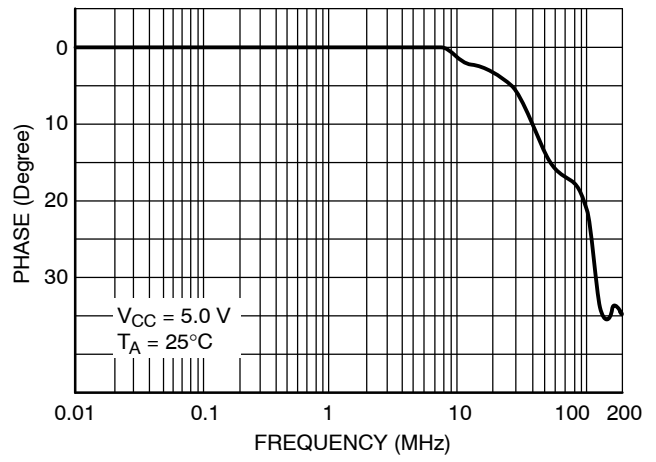


Figure 11. Phase vs. Frequency

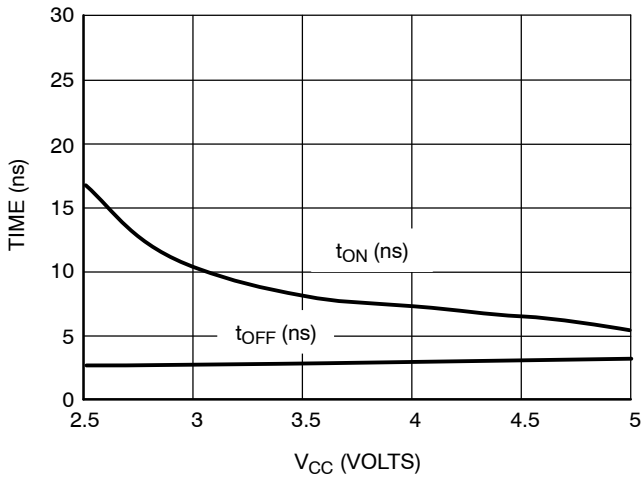


Figure 12. t_{ON} and t_{OFF} vs. V_{CC} at 25°C

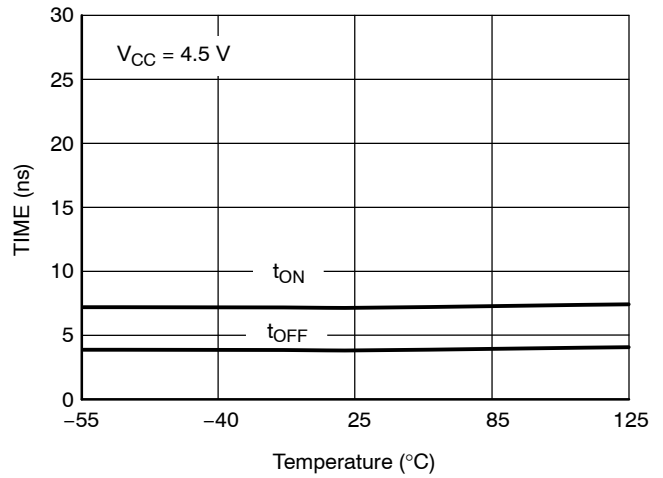


Figure 13. t_{ON} and t_{OFF} vs. Temp

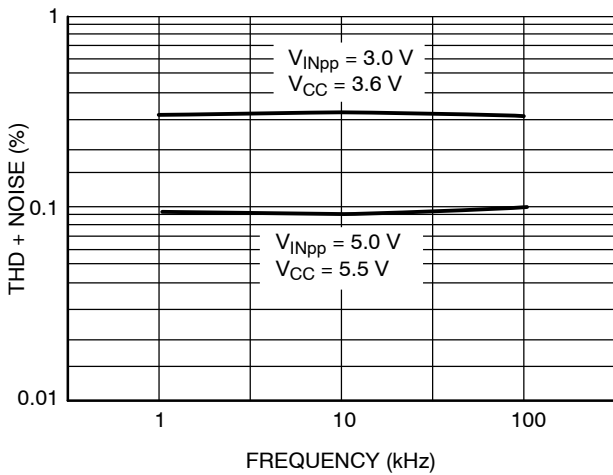


Figure 14. Total Harmonic Distortion Plus Noise vs. Frequency

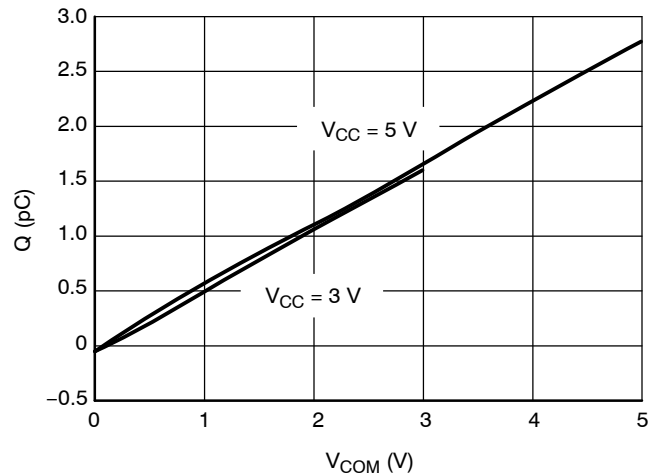


Figure 15. Charge Injection vs. COM Voltage



Figure 16. I_{CC} vs. Temp, $V_{CC} = 3\text{ V}$ & 5 V



Figure 17. R_{ON} vs. V_{CC} , Temp = 25°C



Figure 18. R_{ON} vs Temp, $V_{CC} = 2.0\text{ V}$



Figure 19. R_{ON} vs. Temp, $V_{CC} = 2.5\text{ V}$



Figure 20. R_{ON} vs. Temp, $V_{CC} = 3.0\text{ V}$



Figure 21. R_{ON} vs. Temp, $V_{CC} = 4.5\text{ V}$

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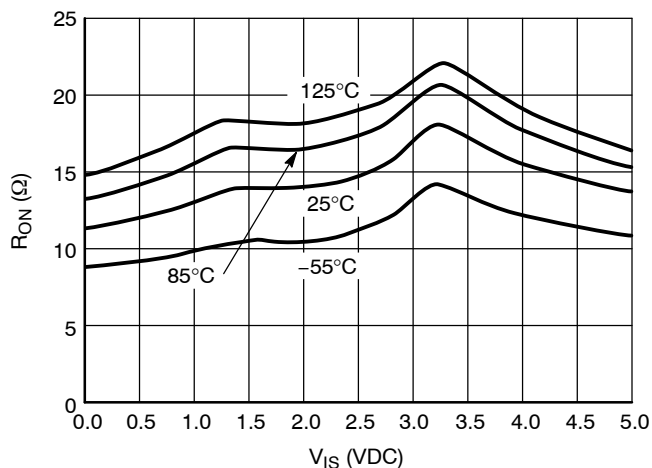


Figure 22. R_{ON} vs. Temp, $V_{CC} = 5.0$ V

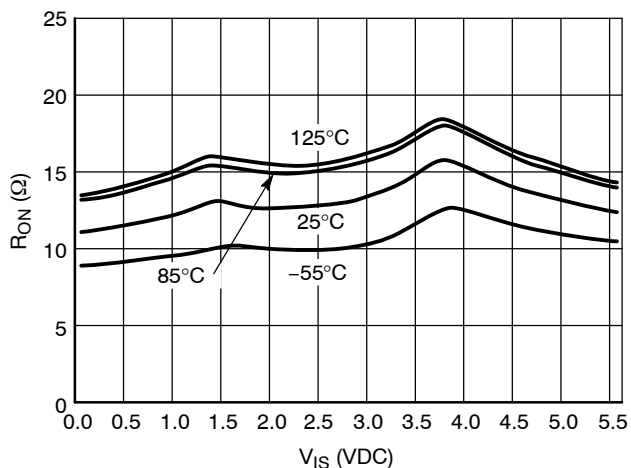


Figure 23. R_{ON} vs. Temp, $V_{CC} = 5.5$ V

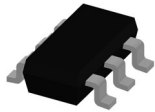
ORDERING INFORMATION

Device	Device Nomenclature				Package	Shipping [†]
	Circuit Indicator	Technology	Device Function	Suffix		
NLAS4599DFT2	NL	AS	DF	T2	SC-88	3000 / Tape & Reel
NLAS4599DFT2G	NL	AS	DF	T2G	SC-88 (Pb-Free)	3000 / Tape & Reel
NLAS4599DTT1	NL	AS	DT	T1	TSOP-6	3000 / Tape & Reel
NLAS4599DTT1G	NL	AS	DT	T1G	TSOP-6 (Pb-Free)	3000 / Tape & Reel
NLVA4599DFT2	NL	AS	DF	T2	SC-88	3000 / Tape & Reel
NLVA4599DFT2G	NL	AS	DF	T2G	SC-88 (Pb-Free)	3000 / Tape & Reel
NLVA4599DTT1G	NL	AS	DT	T1G	TSOP-6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

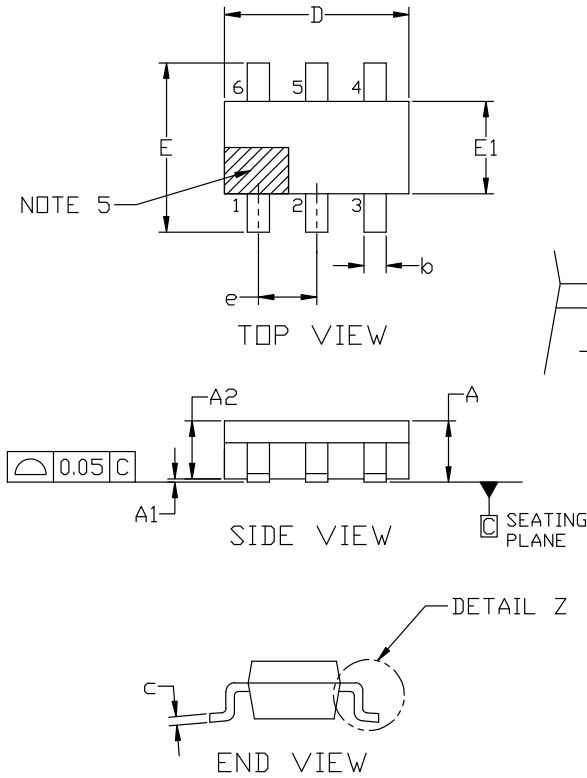
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



TSOP-6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

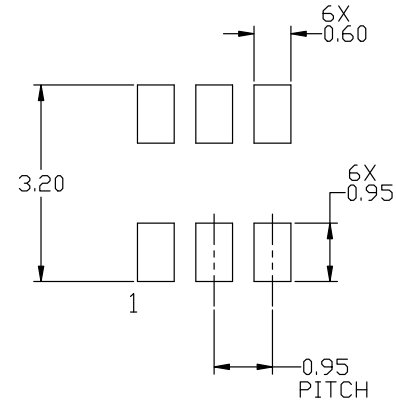
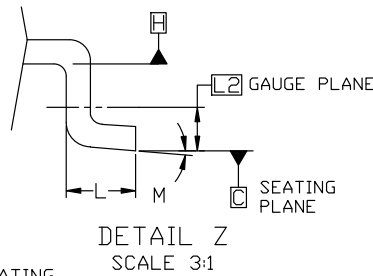
DATE 26 FEB 2024



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
A2	0.80	0.90	1.00
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	---	10°



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

DOCUMENT NUMBER:	98ASB14888C	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TSOP-6 3.00x1.50x0.90, 0.95P	PAGE 1 OF 2

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MECHANICAL CASE OUTLINE

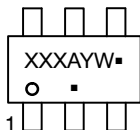
PACKAGE DIMENSIONS



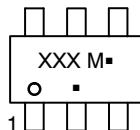
TSOP-6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

DATE 26 FEB 2024

GENERIC MARKING DIAGRAM*



IC



STANDARD

XXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb-Free Package

XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:

- PIN 1. DRAIN
- 2. DRAIN
- 3. GATE
- 4. SOURCE
- 5. DRAIN
- 6. DRAIN

STYLE 2:

- PIN 1. EMITTER 2
- 2. BASE 1
- 3. COLLECTOR 1
- 4. EMITTER 1
- 5. BASE 2
- 6. COLLECTOR 2

STYLE 3:

- PIN 1. ENABLE
- 2. N/C
- 3. R BOOST
- 4. Vz
- 5. V in
- 6. V out

STYLE 4:

- PIN 1. N/C
- 2. V in
- 3. NOT USED
- 4. GROUND
- 5. ENABLE
- 6. LOAD

STYLE 5:

- PIN 1. EMITTER 2
- 2. BASE 2
- 3. COLLECTOR 1
- 4. EMITTER 1
- 5. BASE 1
- 6. COLLECTOR 2

STYLE 6:

- PIN 1. COLLECTOR
- 2. COLLECTOR
- 3. BASE
- 4. EMITTER
- 5. COLLECTOR
- 6. COLLECTOR

STYLE 7:

- PIN 1. COLLECTOR
- 2. COLLECTOR
- 3. BASE
- 4. N/C
- 5. COLLECTOR
- 6. EMITTER

STYLE 8:

- PIN 1. Vbus
- 2. D(in)
- 3. D(in)+
- 4. D(out)+
- 5. D(out)
- 6. GND

STYLE 9:

- PIN 1. LOW VOLTAGE GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN
- 5. DRAIN
- 6. HIGH VOLTAGE GATE

STYLE 10:

- PIN 1. D(OUT)+
- 2. GND
- 3. D(OUT)-
- 4. D(IN)-
- 5. VBUS
- 6. D(IN)+

STYLE 11:

- PIN 1. SOURCE 1
- 2. DRAIN 2
- 3. DRAIN 2
- 4. SOURCE 2
- 5. GATE 1
- 6. DRAIN 1/GATE 2

STYLE 12:

- PIN 1. I/O
- 2. GROUND
- 3. I/O
- 4. I/O
- 5. VCC
- 6. I/O

STYLE 13:

- PIN 1. GATE 1
- 2. SOURCE 2
- 3. GATE 2
- 4. DRAIN 2
- 5. SOURCE 1
- 6. DRAIN 1

STYLE 14:

- PIN 1. ANODE
- 2. SOURCE
- 3. GATE
- 4. CATHODE/DRAIN
- 5. CATHODE/DRAIN
- 6. CATHODE/DRAIN

STYLE 15:

- PIN 1. ANODE
- 2. SOURCE
- 3. GATE
- 4. DRAIN
- 5. N/C
- 6. CATHODE

STYLE 16:

- PIN 1. ANODE/CATHODE
- 2. BASE
- 3. EMITTER
- 4. COLLECTOR
- 5. ANODE
- 6. CATHODE

STYLE 17:

- PIN 1. EMITTER
- 2. BASE
- 3. ANODE/CATHODE
- 4. ANODE
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